

2826



PATENT
Customer No. 22,852
Attorney Docket No. 04329.2306

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Yoshio OZAWA, et al.

Serial No.: 09/559,757

Filed: April 27, 2000

For: SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURE
THEREOF

)
)
) Group Art Unit: 2826
)
) Examiner: Mondt, Johannes P.
)
)
)

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

Supplementary to the Request for Continued Examination (RCE) filed on May 29, 2002,
please amend the application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Twice Amended) A semiconductor device comprising:
a semiconductor substrate having a main plane in which a channel of a transistor is
formed, the semiconductor substrate comprising a first region and a second region defined in a
section taken along a direction of a channel length, the second region having a surface located
lower than that of the first region, and the second region being connected to the first region;
a gate insulating film formed on the first region and containing silicon, nitrogen and
oxygen;

#1613
6/13/02
RECEIVED
JUN 10 2002
TECHNOLOGY CENTER 2800

SUB C17
B1

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com